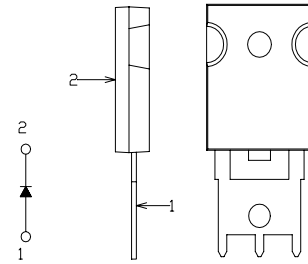


# FRD Type : KSF30A20E

OUTLINE DRAWING

構造 : 拡散型シリコンダイオード(F R D)  
 Construction: Diffusion-type Silicon Diode

用途 : 高周波整流用  
 Application : High Frequency Rectification



## 最大定格 / Maximum Ratings

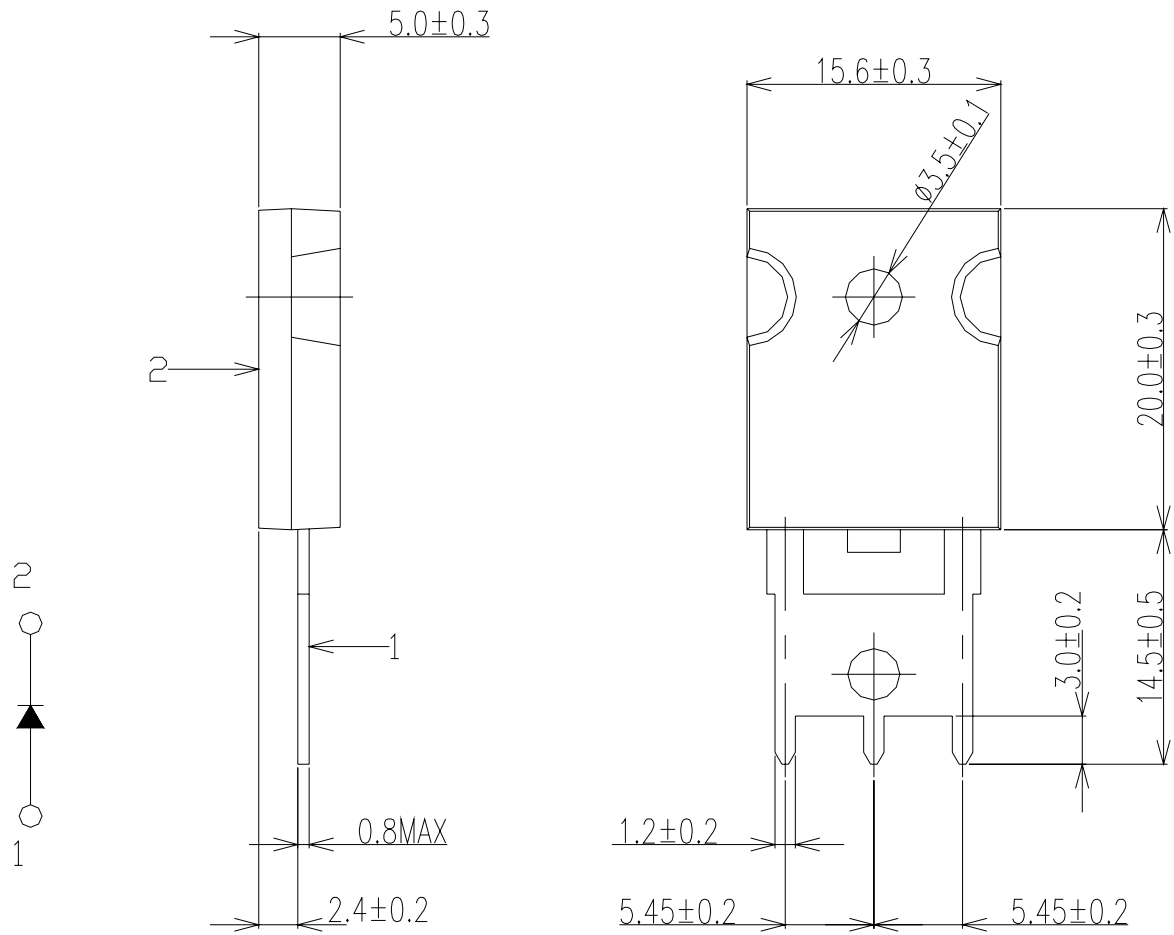
Approx Net Weight:6g

Rating	Symbol	KSF30A20E			Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	$V_{RRM}$	200			V
平均整流電流 Average Rectified Output Current	$I_O$	30	$T_c=101$	50 Hz、正弦半波通電抵抗負荷 Half Sine Wave Resistive Load	A
実効順電流 RMS Forward Current	$I_{F(RMS)}$	47			A
サージ順電流 Surge Forward Current	$I_{FSM}$	400	50 Hz 正弦半波, 1サイクル, 非くり返し Half Sine Wave, 1cycle, Non-repetitive		A
動作接合温度範囲 Operating Junction Temperature Range	$T_{jw}$	- 40 ~ + 150			
保存温度範囲 Storage Temperature Range	$T_{stg}$	- 40 ~ + 150			
締め付けトルク Mounting torque		0.5	推奨値 Recommended value		N·m

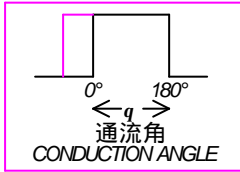
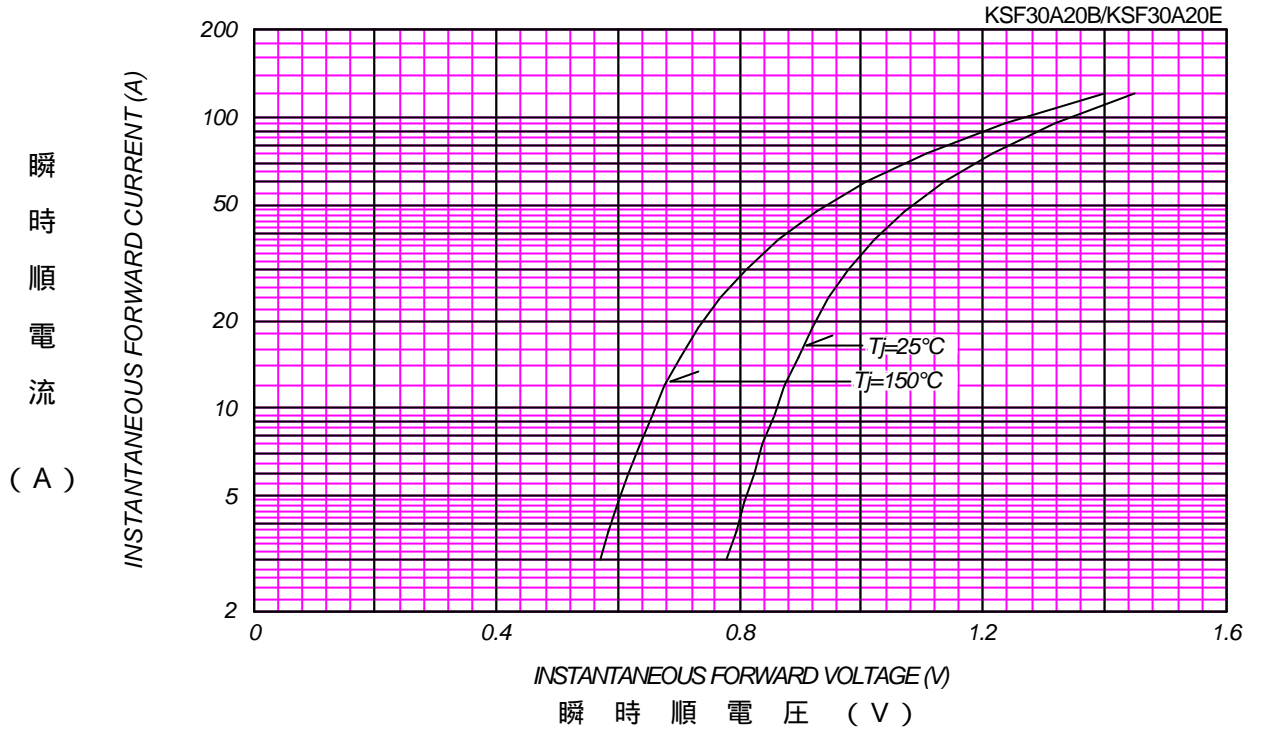
## 電氣的・熱的特性 / Electrical · Thermal Characteristics

Characteristics	Symbol	Conditions	Mni.	Typ.	Max.	Unit
ピーク逆電流 Peak Reverse Current	$I_{RM}$	$T_j = 25$ , $V_{RM} = V_{RRM}$	-	-	25	$\mu A$
ピーク順電圧 * Peak Forward Voltage	$V_{FM}$	$T_j = 25$ , $I_{FM} = 30 A$	-	-	0.98	V
逆回復時間 Reverse Recovery Time	$t_{rr}$	$I_{FM} = 10 A$ , $-di/dt = 50 A/\mu s$ , $T_a = 25$	-	-	50	ns
熱抵抗 Thermal Resistance	$R_{th(j-c)}$	接合部・ケース間 Junction to Case	-	-	1.4	/W

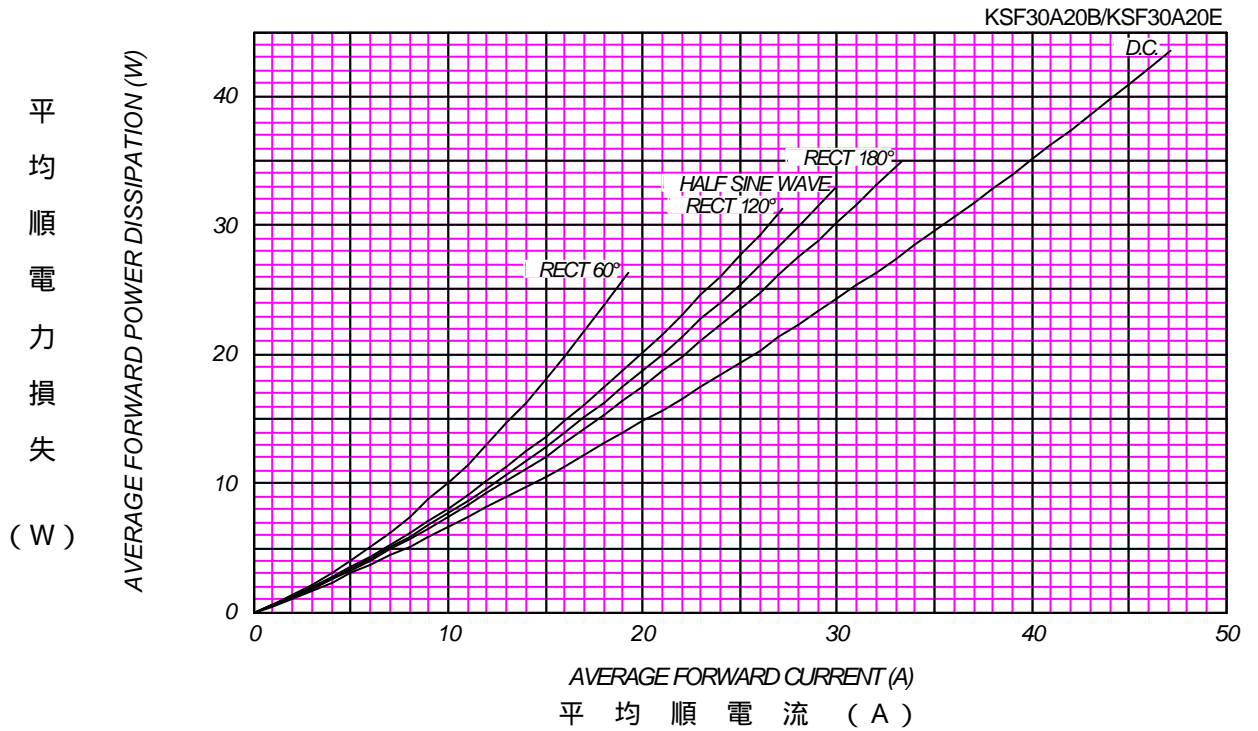
KSF30A20E外形図 (mm)

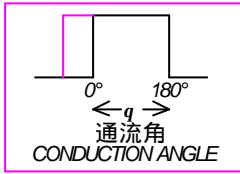


順電压特性  
FORWARD CURRENT VS. VOLTAGE

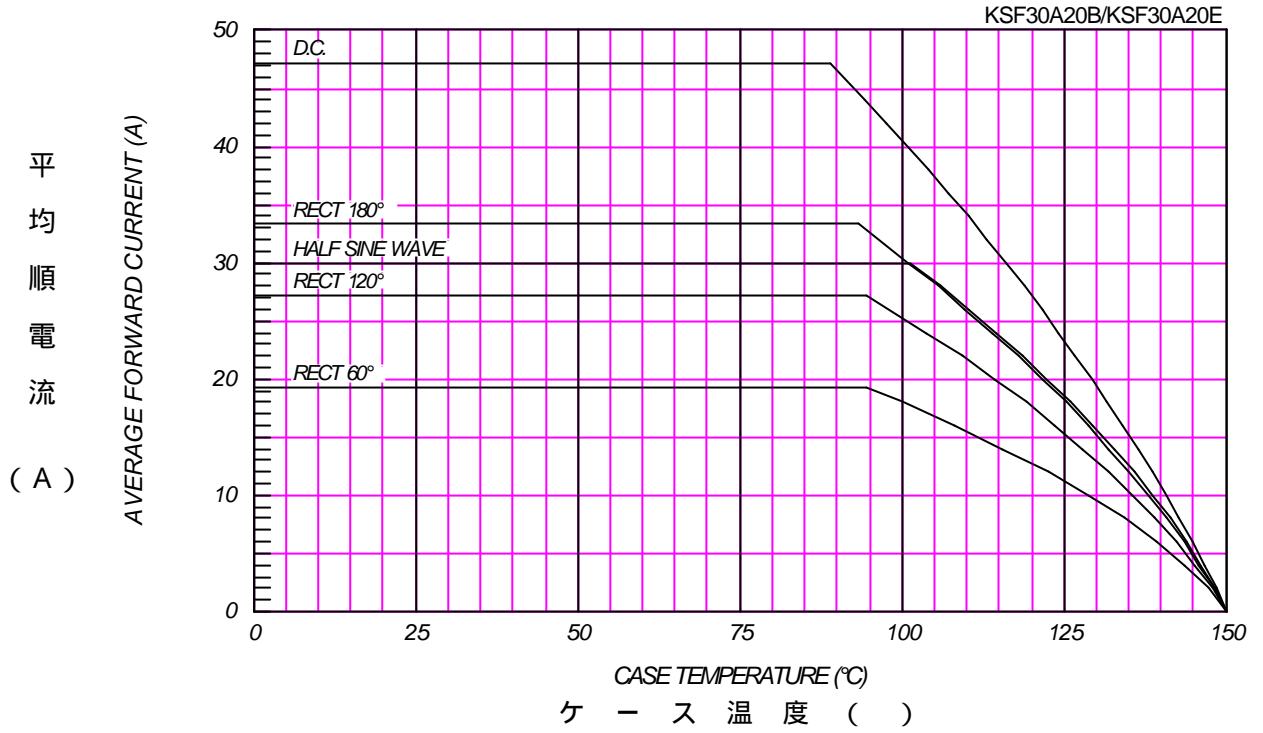


平均順電力損失特性  
AVERAGE FORWARD POWER DISSIPATION





平均順電流 - ケース温度定格  
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE



サージ順電流定格  
SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

